**Product data sheet** 

# 1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO92) plastic package intended for use in low power SMPS emitter switching circuits.

### 2. Features and benefits

- Fast switching
- · High base current drive capability
- High voltage capability
- Very low switching and conduction losses

# 3. Applications

- Emitter-switched low power SMPS circuits
- Self Oscillating Power Supplies
- AC-DC converters
- DC-AC inverters

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>C</sub>	collector current	DC		-	-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>		-	-	2	W
T <sub>j</sub>	junction temperature			-	-	150	°C
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-	700	V
Static characteristics							
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 5; Fig. 6		12	22	32	
		$V_{CE}$ = 5 V; $I_{C}$ = 100 mA; $T_{lead}$ = 25 °C; Fig. 5; Fig. 6		14	24	34	
		$V_{CE}$ = 5 V; $I_{C}$ = 0.75 A; $T_{lead}$ = 25 °C; Fig. 5; Fig. 6		12	15.5	20	





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В
3	В	base		- <b>/</b> -
			3 2 1 <b>TO-92 (SOT54)</b>	sym123

# 6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
TB100	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

# 7. Marking

Table 4. Marking codes

Type number	Marking code
TB100	TB100

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
I <sub>C</sub>	collector current	DC	-	1	Α
I <sub>CM</sub>	peak collector current		-	2	Α
I <sub>B</sub>	base current		-	0.5	Α
I <sub>BM</sub>	peak base current		-	3	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	-	2	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C

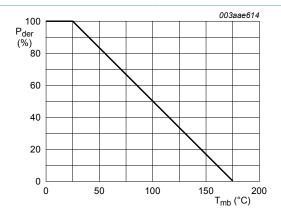


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

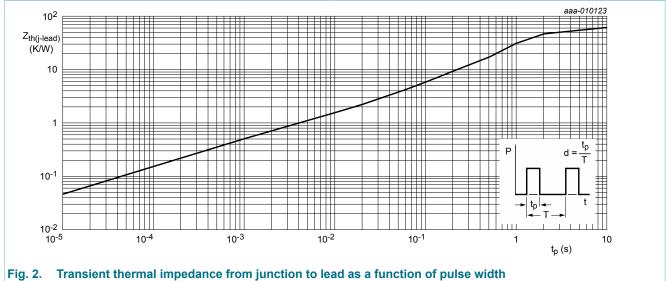
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

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## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead		-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted; lead length = 4 mm; Fig. 2	-	150	-	K/W



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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>lead</sub> = 25 °C	-	0.8	100	μA
	current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	-	2	500	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 9 V; I <sub>C</sub> = 0 A; T <sub>lead</sub> = 25 °C	-	0.05	100	μΑ
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 0.75 \text{ A}$ ; $I_B = 0.15 \text{ A}$ ; $T_{lead} = 25 ^{\circ}\text{C}$ ; Fig. 3	-	0.24	1	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 0.75 \text{ A}; I_B = 0.15 \text{ A}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 4	-	0.93	1.3	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; T <sub>lead</sub> = 25 °C; Fig. 5; Fig. 6	12	22	32	
		$I_C$ = 100 mA; $V_{CE}$ = 5 V; $T_{lead}$ = 25 °C; Fig. 5; Fig. 6	14	24	34	
		I <sub>C</sub> = 0.75 A; V <sub>CE</sub> = 5 V; T <sub>lead</sub> = 25 °C; Fig. 5; Fig. 6	12	15.5	20	
Dynamic ch	naracteristics (resistive loa	d)		,		,
t <sub>s</sub>	storage time	I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.2 A; I <sub>Boff</sub> = -0.2 A;	-	2	-	μs
t <sub>f</sub>	fall time	$R_L = 75 \Omega$ ; $V_{BB} = -4 V$ ; $T_{lead} = 25 °C$ ; Fig. 7; Fig. 8	-	320	-	ns

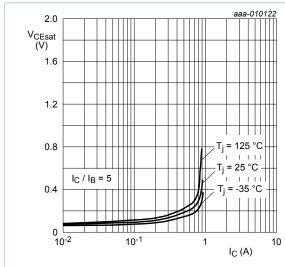


Fig. 3. Collector-emitter saturation voltage as a function of collector current; typical values

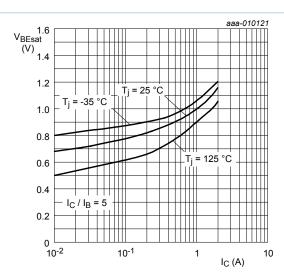


Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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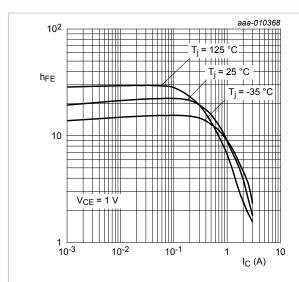


Fig. 5. DC current gain as a function of collector current; typical values

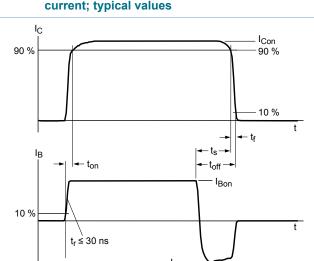


Fig. 7. Switching times waveforms for resistive load

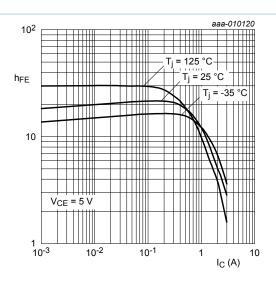


Fig. 6. DC current gain as a function of collector current; typical values

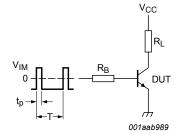


Fig. 8. Test circuit for resistive load switching

$$\begin{split} V_{IM} = & -6 \text{ to } + 8 \text{ V; } V_{CC} = 250 \text{ V; } t_p = 20 \text{ $\mu$s; } \pmb{\delta} = \frac{t_p}{T} = 0.01 \\ R_B \text{ and } R_L \text{ calculated from } I_{Con} \text{ and } I_{Bon} \text{ requirements.} \end{split}$$

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# 11. Package outline

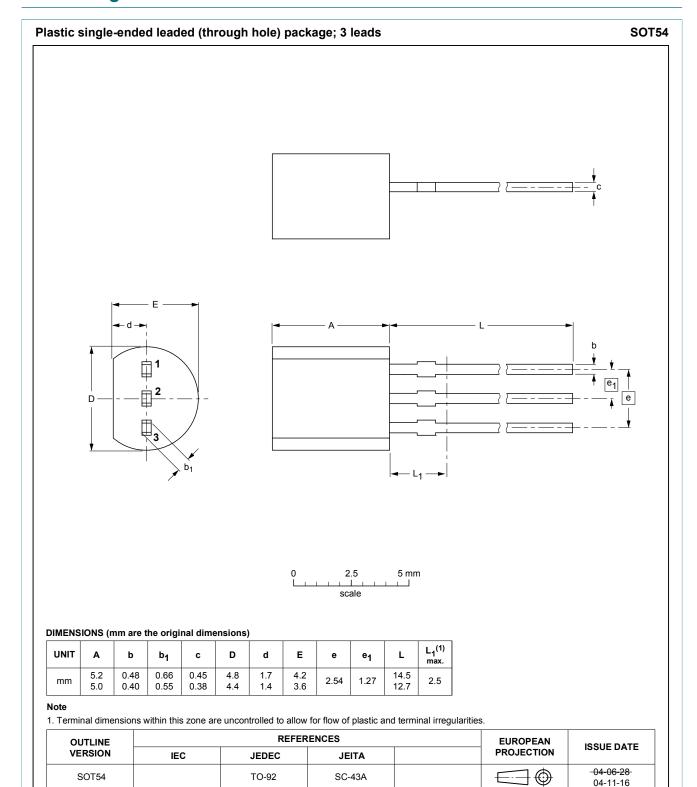


Fig. 9. Package outline TO-92 (SOT54)

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Date of release: 19 December 2013